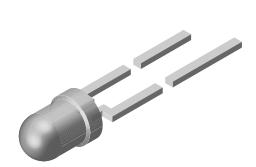
HALOGEN FREE

GREEN



## Vishay Semiconductors

# High Power Infrared Emitting Diode, 940 nm, GaAlAs, MQW



### **DESCRIPTION**

TSAL4400 is an infrared, 940 nm emitting diode in GaAlAs, MQW technology with high radiant power molded in a blue-gray plastic package.

### **FEATURES**

Package type: leadedPackage form: T-1

• Dimensions (in mm): Ø 3

• Peak wavelength:  $\lambda_p = 940 \text{ nm}$ 

High reliability

• High radiant power

• High radiant intensity

• Angle of half intensity:  $\varphi = \pm 25^{\circ}$ 

· Low forward voltage

· Suitable for high pulse current operation

· Good spectral matching with Si photodetectors

• Package matches with detector TEFT4300

 Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912"><u>www.vishay.com/doc?99912</u></a>

### **APPLICATIONS**

- · Infrared remote control units
- Free air transmission systems
- Infrared source for optical counters and card readers

| PRODUCT SUMMARY |                        |       |                             |                     |  |
|-----------------|------------------------|-------|-----------------------------|---------------------|--|
| COMPONENT       | I <sub>e</sub> (mW/sr) | φ (°) | $\lambda_{\mathbf{p}}$ (nm) | t <sub>r</sub> (ns) |  |
| TSAL4400        | 36                     | ± 25  | 940                         | 15                  |  |

#### Note

• Test conditions see table "Basic Characteristics"

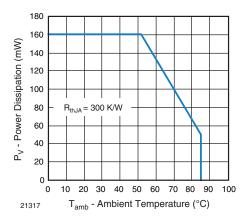
| ORDERING INFORMATION |           |                              |              |  |  |  |
|----------------------|-----------|------------------------------|--------------|--|--|--|
| ORDERING CODE        | PACKAGING | REMARKS                      | PACKAGE FORM |  |  |  |
| TSAL4400             | Bulk      | MOQ: 5000 pcs, 5000 pcs/bulk | T-1          |  |  |  |
| TSAL4400-RSZ         | Ammopack  | MOQ: 8000 pcs, 2000 pcs/box  | T-1          |  |  |  |

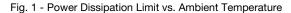
#### Note

• MOQ: minimum order quantity

| <b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>amb</sub> = 25 °C, unless otherwise specified) |  |                   |                     |      |  |
|--|--|-------------------|---------------------|------|--|
| PARAMETER  | TEST CONDITION                         | SYMBOL            | VALUE               | UNIT |  |
| Reverse voltage  |  | $V_R$             | 5                   | V    |  |
| Forward current  |  | I <sub>F</sub>    | 100                 | mA   |  |
| Peak forward current   | $t_p/T = 0.5$ , $t_p = 100 \mu s$      | I <sub>FM</sub>   | I <sub>FM</sub> 200 |      |  |
| Surge forward current  | t <sub>p</sub> = 100 μs                | I <sub>FSM</sub>  | 1.5                 | Α    |  |
| Power dissipation  |  | P <sub>V</sub>    | 160                 | mW   |  |
| Junction temperature   |  | Tj                | 100                 | °C   |  |
| Operating temperature range  |  | T <sub>amb</sub>  | -40 to +85          | °C   |  |
| Storage temperature range  |  | T <sub>stg</sub>  | -40 to +100         | °C   |  |
| Soldering temperature  | t ≤ 5 s, 2 mm from case                | T <sub>sd</sub>   | 260                 | °C   |  |
| Thermal resistance junction / ambient  | J-STD-051, leads 7 mm, soldered on PCB | R <sub>thJA</sub> | 300                 | K/W  |  |







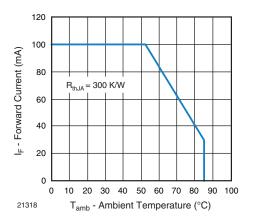


Fig. 2 - Forward Current Limit vs. Ambient Temperature

| <b>BASIC CHARACTERISTICS</b> (T <sub>amb</sub> = 25 °C, unless otherwise specified) |   |                  |      |      |      |       |
|---|---|------------------|------|------|------|-------|
| PARAMETER   | TEST CONDITION                                  | SYMBOL           | MIN. | TYP. | MAX. | UNIT  |
| Farmered voltage  | $I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$     | V <sub>F</sub>   | -    | 1.35 | 1.6  | V     |
| Forward voltage   | $I_F = 1 \text{ A}, t_p = 100 \mu \text{s}$     | V <sub>F</sub>   | -    | 2.6  | 3    | V     |
| Temperature coefficient of V <sub>F</sub>   | I <sub>F</sub> = 1 mA                           | TK <sub>VF</sub> | -    | -1.8 | -    | mV/K  |
| Reverse current   | V <sub>R</sub> = 5 V                            | I <sub>R</sub>   | -    | -    | 10   | μΑ    |
| Junction capacitance  | $V_R = 0 \text{ V, } f = 1 \text{ MHz, } E = 0$ | C <sub>j</sub>   | -    | 60   | -    | pF    |
| Radiant intensity   | $I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$     | l <sub>e</sub>   | 16   | 36   | 80   | mW/sr |
|   | $I_F = 1 \text{ A}, t_p = 100 \mu \text{s}$     | l <sub>e</sub>   | 135  | 290  | -    | mW/sr |
| Radiant power   | $I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$     | фe               | -    | 40   | -    | mW    |
| Temperature coefficient of φ <sub>e</sub>   | I <sub>F</sub> = 20 mA                          | TKφ <sub>e</sub> | -    | -0.6 | -    | %/K   |
| Angle of half intensity   |   | φ                | -    | ± 25 | -    | 0     |
| Peak wavelength   | I <sub>F</sub> = 100 mA                         | $\lambda_{p}$    | -    | 940  | -    | nm    |
| Spectral bandwidth  | I <sub>F</sub> = 100 mA                         | Δλ               | -    | 25   | -    | nm    |
| Temperature coefficient of λ <sub>p</sub>   | I <sub>F</sub> = 100 mA                         | TKλ <sub>p</sub> | -    | 0.25 | -    | nm/K  |
| Rise time   | I <sub>F</sub> = 100 mA                         | t <sub>r</sub>   | -    | 15   | -    | ns    |
| Fall time   | I <sub>F</sub> = 100 mA                         | t <sub>f</sub>   | -    | 15   | -    | ns    |

## **BASIC CHARACTERISTICS** (T<sub>amb</sub> = 25 °C, unless otherwise specified)

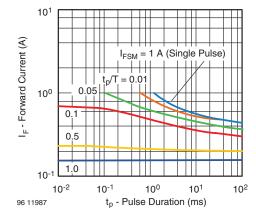


Fig. 3 - Pulse Forward Current vs. Pulse Duration

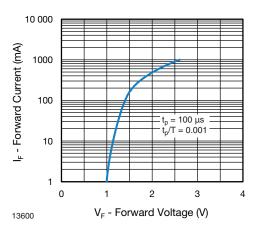


Fig. 4 - Forward Current vs. Forward Voltage

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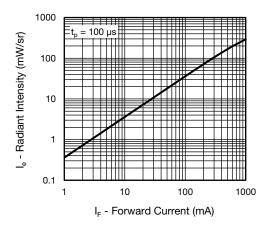


Fig. 5 - Radiant Intensity vs. Forward Current

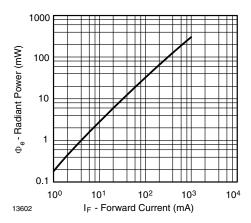


Fig. 6 - Radiant Power vs. Forward Current

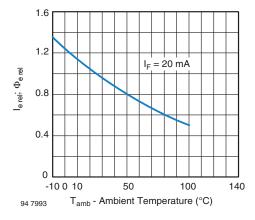


Fig. 7 - Rel. Radiant Intensity/Power vs. Ambient Temperature

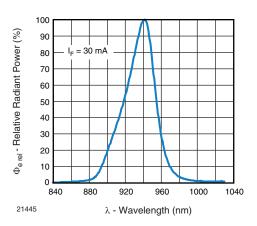


Fig. 8 - Relative Radiant Power vs. Wavelength

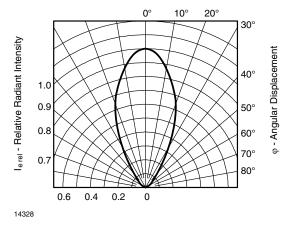
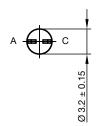
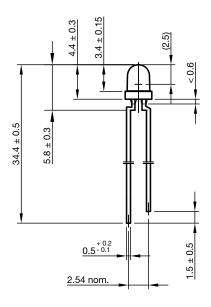


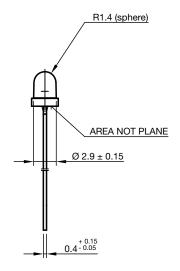
Fig. 9 - Relative Radiant Intensity vs. Angular Displacement

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### **PACKAGE DIMENSIONS** in millimeters









Drawing-No.: 6.544-5255.01-4

Issue: 9; 28.07.14



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